

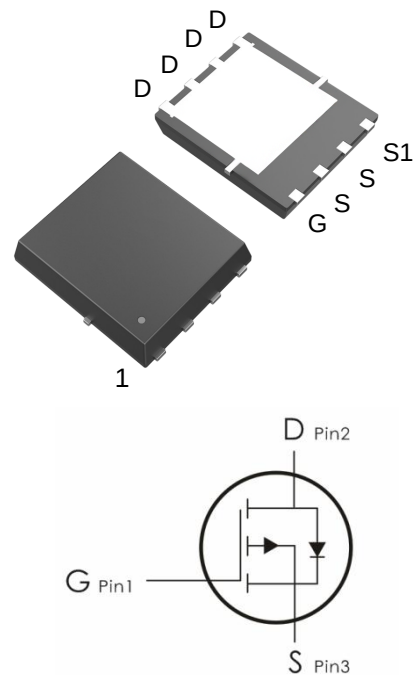
Description:

This P-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=-100V, I_D=-20A, R_{DS(on)} < 100m\Omega @ V_{GS}=-10V$ (Typ: $80m\Omega$)
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.
- 6) MSL3



Package Marking and Ordering Information:

Part NO.	Marking	Package	Packing
DON20P10	20P10	DFN5*6-8	5000 pcs/Reel

Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	-100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current	-20	A
	Continuous Drain Current- $T_C=100^\circ C$	-14	
I_{DM}	Pulsed Drain Current ¹	-80	
P_D	Power Dissipation	62.5	W
E_{AS}	Single pulse avalanche energy ²	72	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55-+150	$^\circ C$

Thermal Characteristics:

Symbol	Parameter	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2	$^\circ C/W$

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V,I _D =250 μ A	-100	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-100V	---	---	-1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 20V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	-1	-1.9	-2.5	V
R _{DS(ON)}	Drain-Source On Resistance ³	V _{GS} =-10V,I _D =-3A	---	80	100	m Ω
		V _{GS} =-4.5V,I _D =-2A	---	90	120	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-25V, V _{GS} =0V, f=1MHz	---	4077	---	pF
C _{oss}	Output Capacitance		---	119	--	
C _{rss}	Reverse Transfer Capacitance		---	92	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DS} =-50V, I _D =-3A, R _G =3 Ω ,V _{GS} =-10V	---	26	---	ns
t _r	Rise Time		---	36.7	---	ns
t _{d(off)}	Turn-Off Delay Time		---	152	---	ns
t _f	Fall Time		---	94	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DS} =-50V, I _D =-3A	---	52	---	nC
Q _{gs}	Gate-Source Charge		---	8	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	9	---	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage	V _{GS} =0V, I _{SD} =-4A	---	---	-1.2	V
I _S	Continuous Drain Curren	V _D =V _G =0V	---	---	-20	A
I _{SM}	Pulsed Drain Current		---	---	-80	A
T _{rr}	Reverse Recovery Time	I _F =-3A,T _J =25℃	---	60	---	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/us	---	145	---	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J = 25^\circ\text{C}$, $V_{DD} = -50\text{V}$, $V_G = -10\text{V}$, $R_G = 25\Omega$, $L = 0.5\text{mH}$.
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Test Circuit

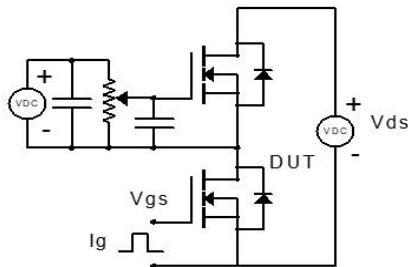


Figure 1: Gate Charge Test Circuit & Waveform

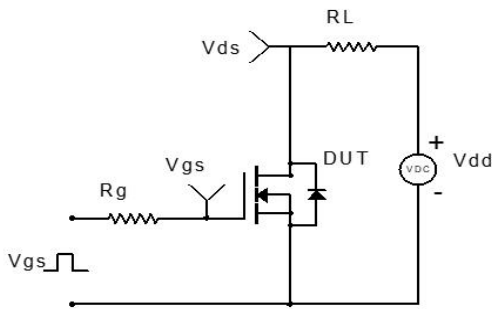
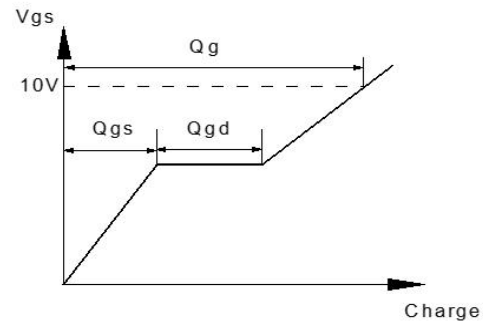


Figure 2: Resistive Switching Test Circuit & Waveform

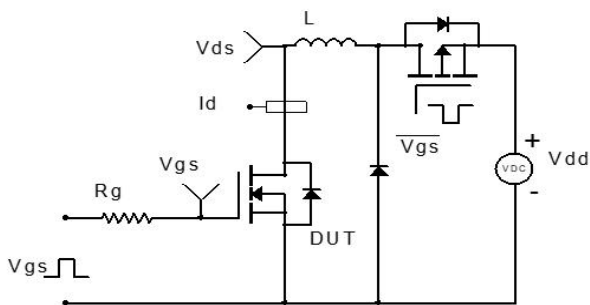
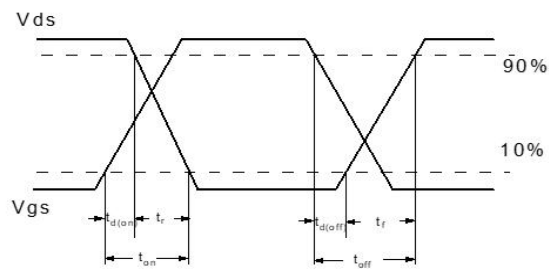


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform

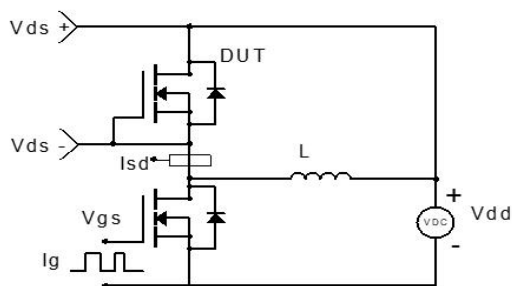
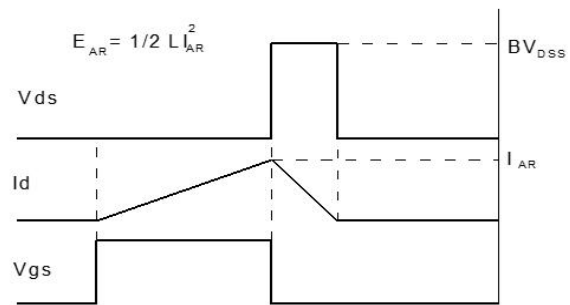
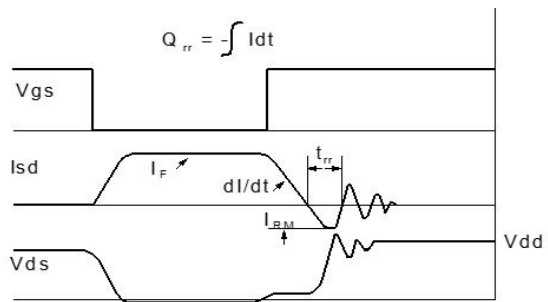
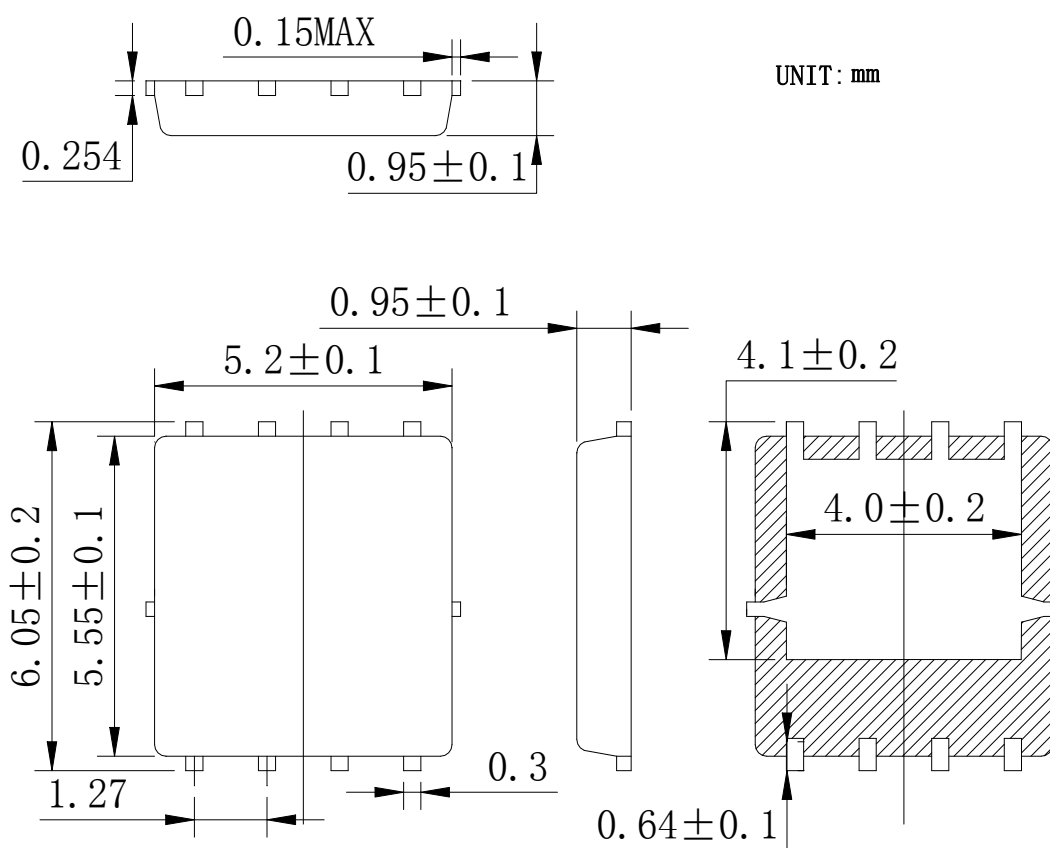


Figure 4: Diode Recovery Test Circuit & Waveform

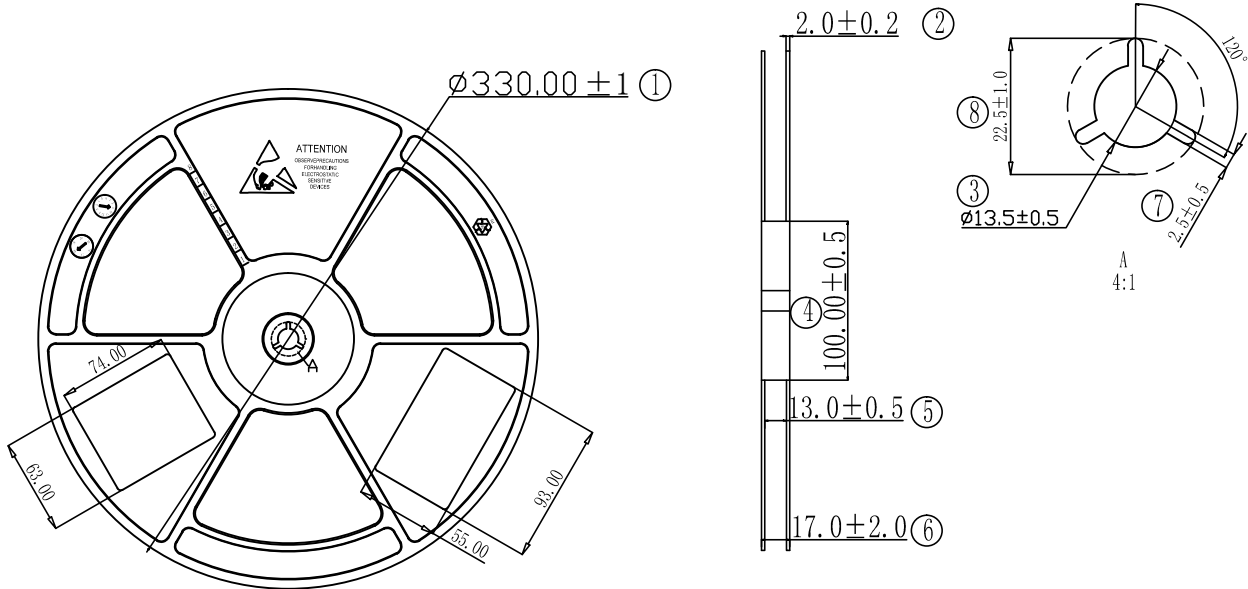


DFN5x6-8 Package Information:

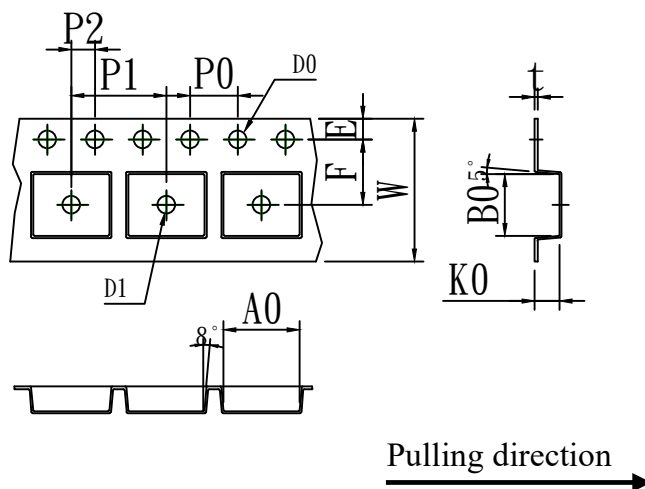


Tape & Reel Information

Dimensions in mm



Symbol	A0	B0	K0	D0	D1	P0	P1	10*P0
Spec	6.15±0.10	5.40±0.10	1.30±0.10	1.55±0.10	1.55±0.10	4.00±0.10	8.00±0.10	40.00±0.10
Symbol	W	E	F	P2	t			
Spec	12.00±0.10	1.75±0.10	5.50±0.10	2.00±0.10	0.20±0.05			



Marking Information:

①. Doingter LOGO

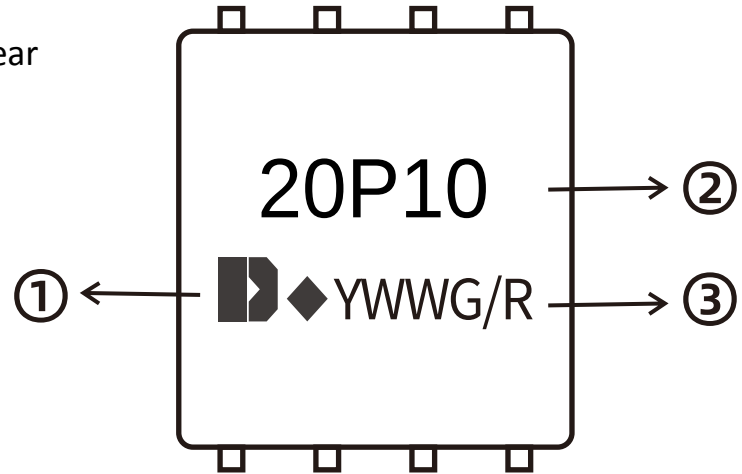
②. Part NO.

③. Date Code(YWWG / R)

Y : Year Code , last digit of the year

WW : Week Code(01-53)

G/R : G(Green) /R(Lead Free)

**Previous Version**

Version	Date	Subjects (major changes since last revision)
1.0	2024-12-12	Release of final version

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